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Si5853DC
 Vishay Siliconix

P-Channel 1.8 V (G-S) MOSFET with Schottky Diode

MOSFET PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 20	0.110 at $V_{GS} = - 4.5$ V	- 3.6
	0.160 at $V_{GS} = - 2.5$ V	- 3.0
	0.240 at $V_{GS} = - 1.8$ V	- 2.4

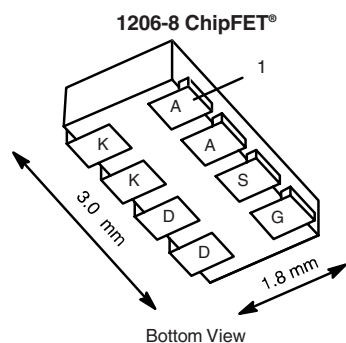
SCHOTTKY PRODUCT SUMMARY		
V_{KA} (V)	V_f (V) Diode Forward Voltage	I_F (A)
20	0.48 V at 0.5 A	1.0

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- LITTLE FOOT® Plus
- Compliant to RoHS Directive 2002/95/EC



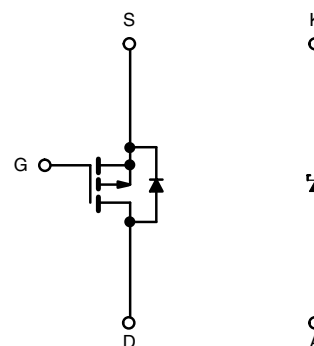
RoHS
 COMPLIANT
 HALOGEN
FREE
 Available



Marking Code

JA	XX
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 Lot Traceability and Date Code
 Part # Code



P-Channel MOSFET

Ordering Information: Si5853DC-T1-E3 (Lead (Pb)-free)
 Si5853DC-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted				
Parameter	Symbol	5 s	Steady State	Unit
Drain-Source Voltage (MOSFET and Schottky)	V_{DS}	- 20		V
Reverse Voltage (Schottky)	V_{KA}	20		V
Gate-Source Voltage (MOSFET)	V_{GS}	± 8	± 8	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) (MOSFET) ^a	I_D	$T_A = 25^\circ\text{C}$	- 3.6	- 2.7
		$T_A = 85^\circ\text{C}$	- 2.6	- 1.9
Pulsed Drain Current (MOSFET)	I_{DM}	- 10		A
Continuous Source Current (MOSFET Diode Conduction) ^a	I_S	- 1.8	- 0.9	
Average Forward Current (Schottky)	I_F	1.0		
Pulsed Forward Current (Schottky)	I_{FM}	7		
Maximum Power Dissipation (MOSFET) ^a	P_D	$T_A = 25^\circ\text{C}$	2.1	1.1
		$T_A = 85^\circ\text{C}$	1.1	0.6
Maximum Power Dissipation (Schottky) ^a	P_D	$T_A = 25^\circ\text{C}$	1.3	0.96
		$T_A = 85^\circ\text{C}$	0.68	0.59
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^{b, c}		260		

Notes:

- Surface mounted on 1" x 1" FR4 board.
- See reliability manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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THERMAL RESISTANCE RATINGS						
Parameter		Device	Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^a	t ≤ 5 s	MOSFET	R _{thJA}	50	60	°C/W
		Schottky		77	95	
	Steady State	MOSFET		90	110	
		Schottky		110	130	
Junction-to-Foot	Steady State	MOSFET	R _{thJF}	30	40	
		Schottky	33	40		

Notes:

a. Surface mounted on 1" x 1" FR4 board.

MOSFET SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.45		- 1.0	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 85 °C			- 5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V	- 10			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 2.7 A		0.095	0.110	Ω
		V _{GS} = - 2.5 V, I _D = - 2.2 A		0.137	0.160	
		V _{GS} = - 1.8 V, I _D = - 1 A		0.205	0.240	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 2.7 A		7		S
Diode Forward Voltage ^a	V _{SD}	I _S = - 0.9 A, V _{GS} = 0 V		- 0.8	- 1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 2.7 A		5.1	7.7	nC
Gate-Source Charge	Q _{gs}		1.2			
Gate-Drain Charge	Q _{gd}		1.0			
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 10 Ω I _D ≅ - 1 A, V _{GEN} = - 4.5 V, R _g = 6 Ω		16	25	ns
Rise Time	t _r		30	45		
Turn-Off Delay Time	t _{d(off)}		30	45		
Fall Time	t _f		27	40		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 0.9 A, di/dt = 100 A/μs		20	40	

Notes:

a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.

b. Guaranteed by design, not subject to production testing.

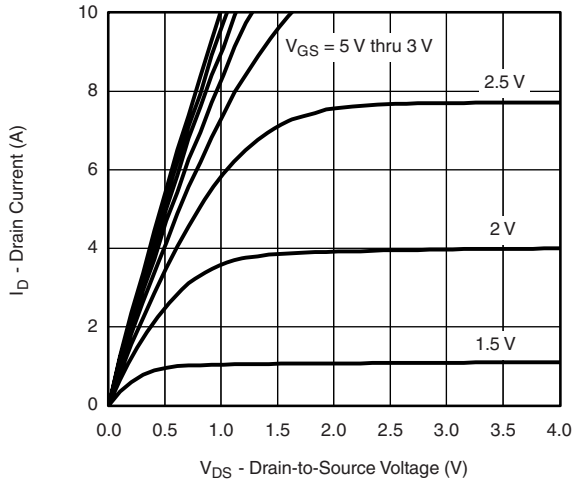
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SCHOTTKY SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage Drop	V _F	I _F = 0.5 A		0.42	0.48	V
		I _F = 0.5 A, T _J = 125 °C		0.33	0.4	
Maximum Reverse Leakage Current	I _{rm}	V _r = 20 V		0.002	0.100	mA
		V _r = 20 V, T _J = 85 °C		0.10	1	
		V _r = 20 V, T _J = 125 °C		1.5	10	
Junction Capacitance	C _T	V _r = 10 V		31		pF

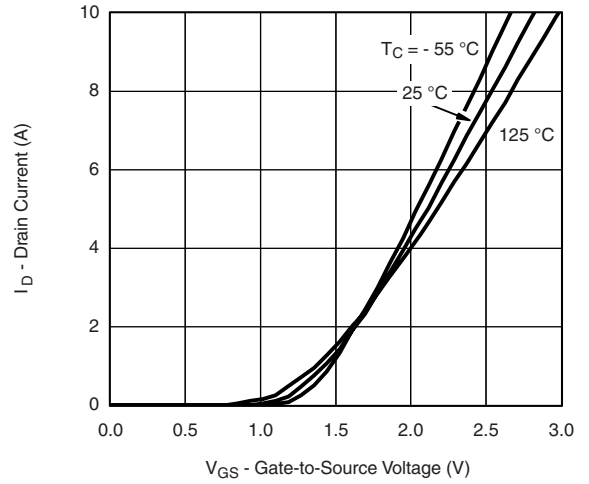


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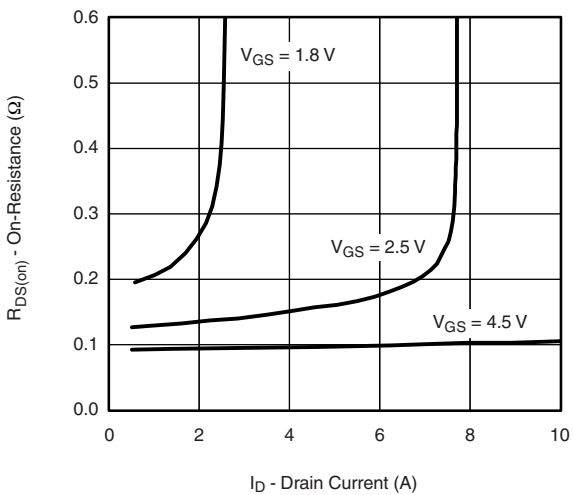
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



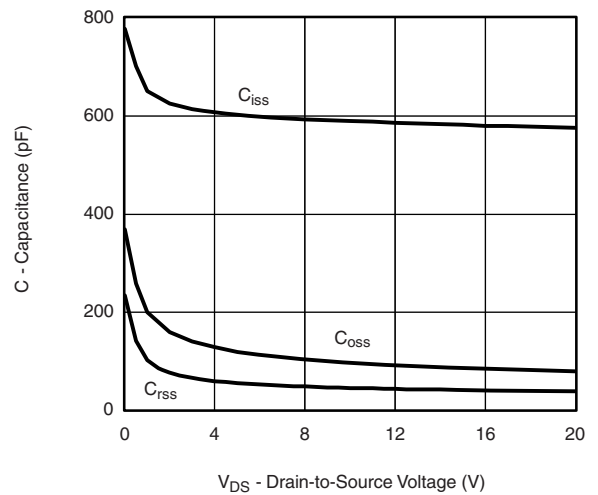
Output Characteristics



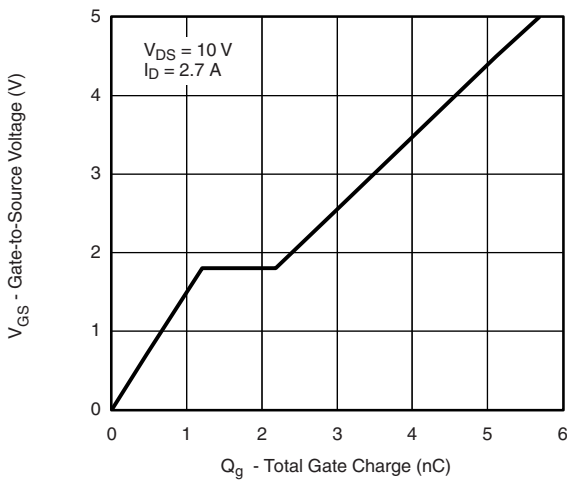
Transfer Characteristics



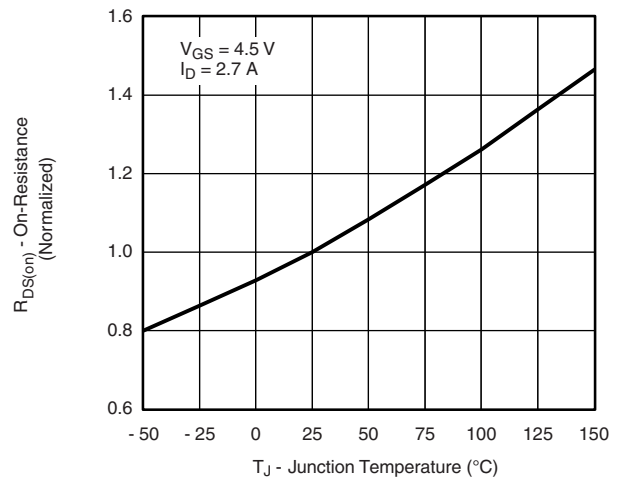
On-Resistance vs. Drain Current



Capacitance



Gate Charge



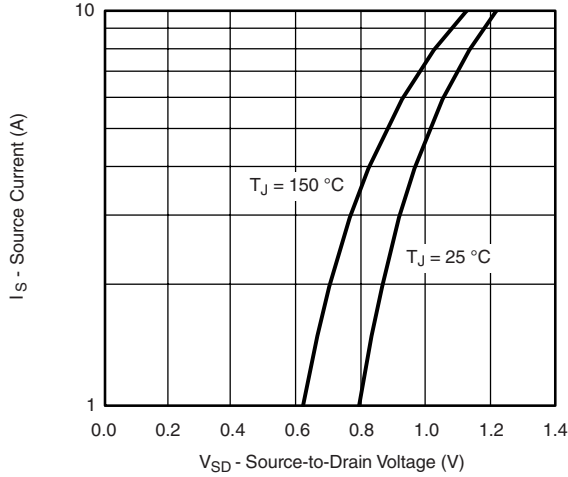
On-Resistance vs. Junction Temperature

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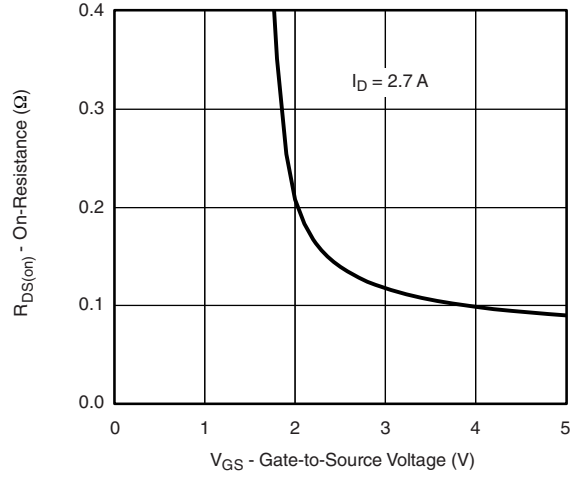
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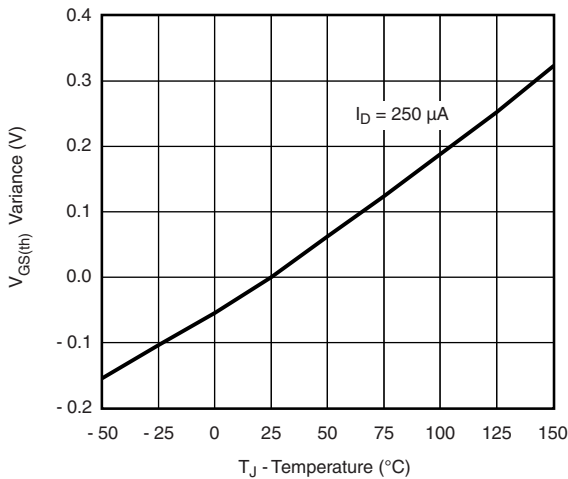
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



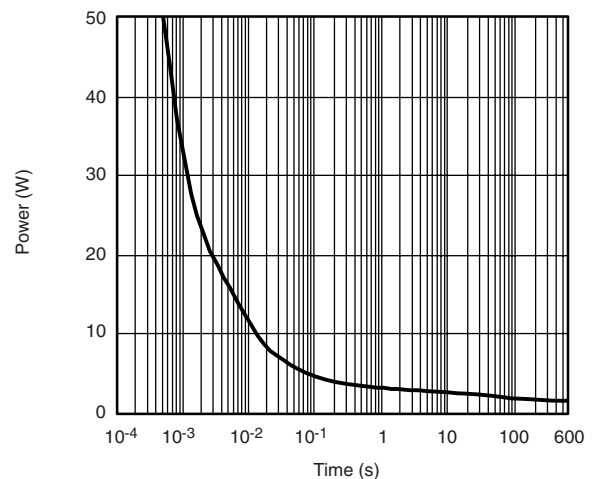
Source-Drain Diode Forward Voltage



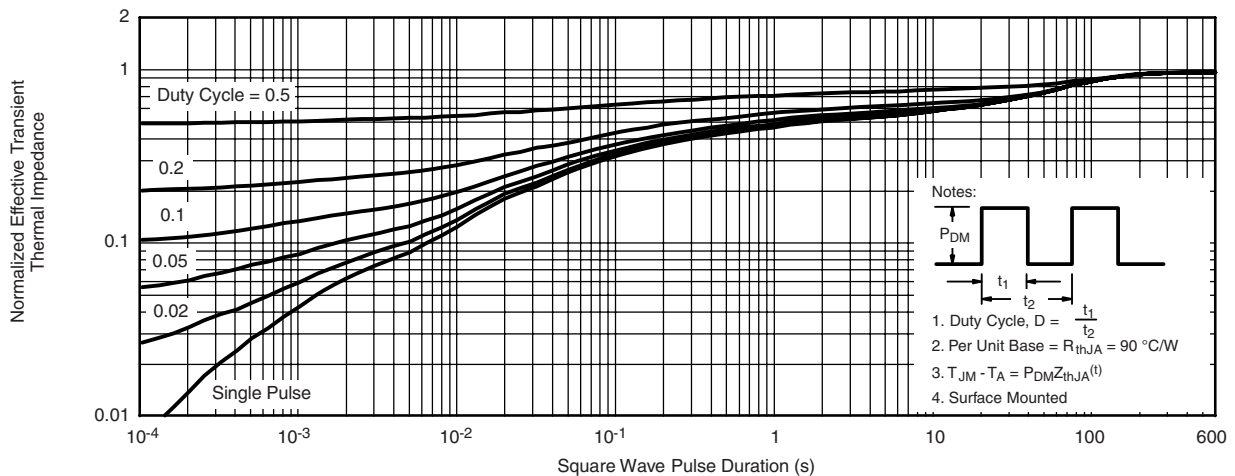
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



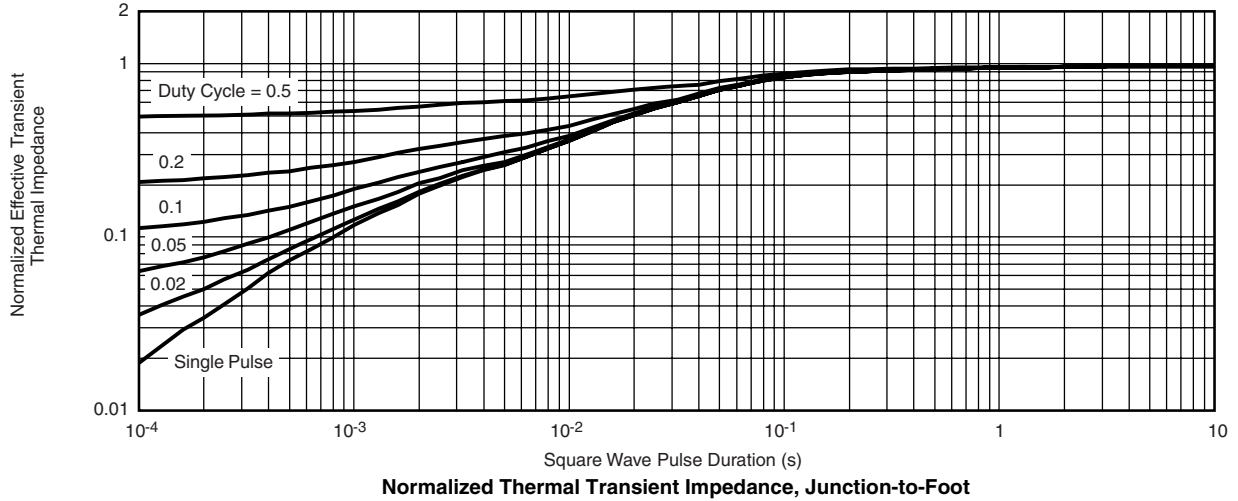
Normalized Thermal Transient Impedance, Junction-to-Ambient

- Notes:
- 1. Duty Cycle, $D = \frac{t_1}{t_2}$
 - 2. Per Unit Base = $R_{thJA} = 90\text{ °C/W}$
 - 3. $T_{JM} - T_A = P_{DM} Z_{thJA}^{(1)}$
 - 4. Surface Mounted

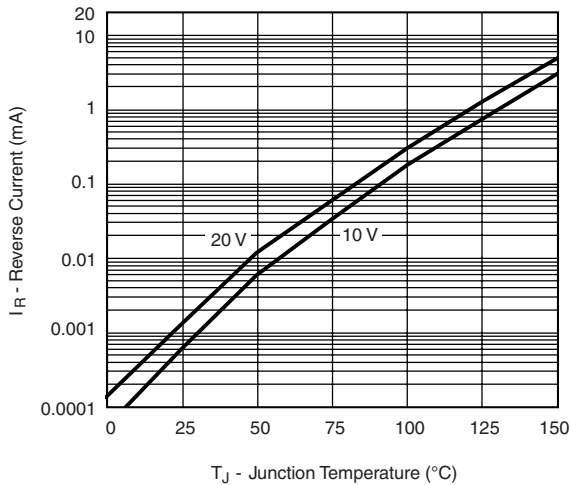


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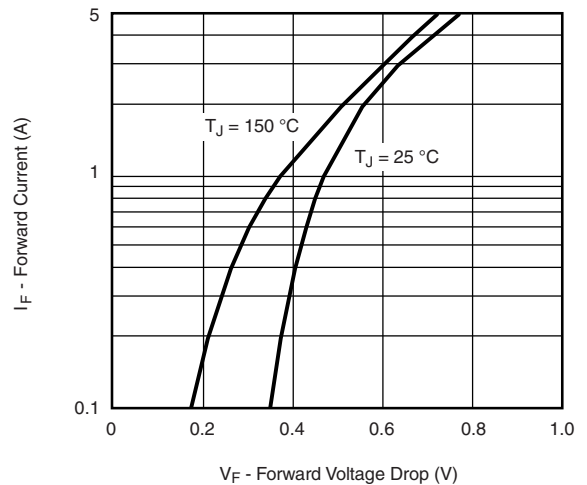
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



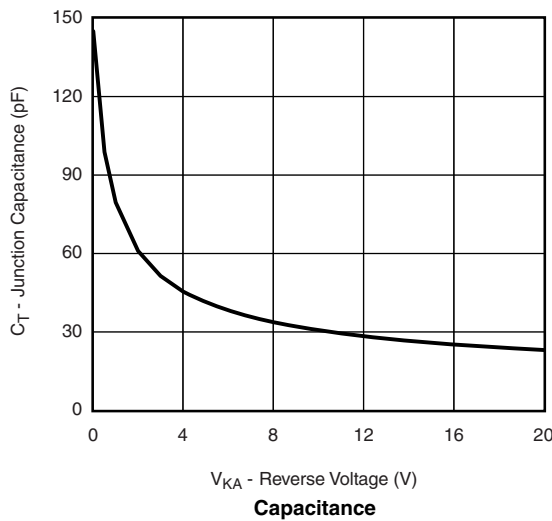
SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Reverse Current vs. Junction Temperature



Forward Voltage Drop



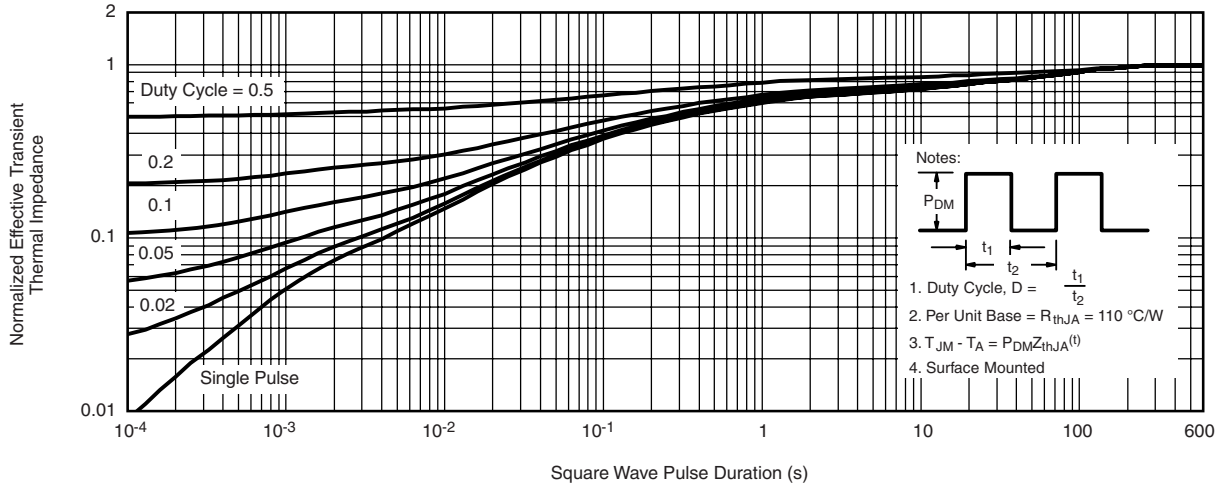
Capacitance

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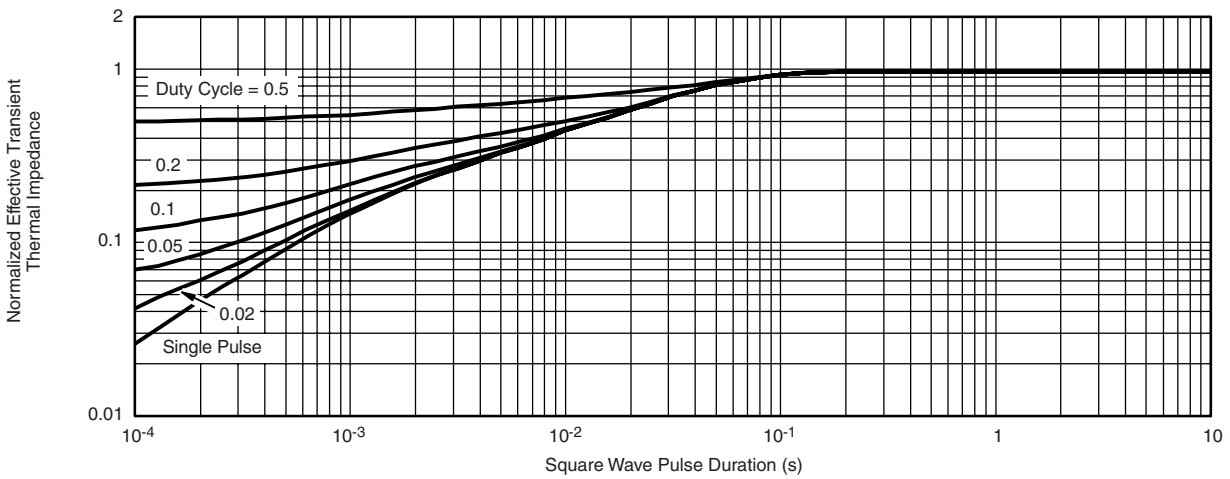
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SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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